

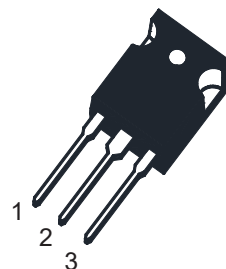
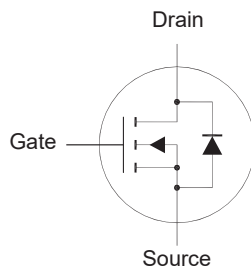
N-Channel Enhancement Mode MOSFET

Features

- Advanced trench cell design
- High speed switch
- Halogen and Antimony Free(HAF),
RoHS compliant

Applications

- Portable appliances
- Power management



TO-247 Plastic Package
1.Gate 2.Drain 3.Source

Key Parameters

Parameter	Value	Unit
BV_{DSS}	60	V
$R_{DS(ON)} \text{ Max}$	3.2 @ $V_{GS} = 10 \text{ V}$	m Ω
$V_{GS(th)} \text{ typ}$	2.8	V
$Q_g \text{ typ}$	82 @ $V_{GS} = 10 \text{ V}$	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Drain-Gate Voltage	V_{GS}	± 20	V
Drain Current - Continuous	I_D	93	A
		58	
Drain Current - Pulsed ¹⁾	I_{DM}	450	A
Avalanche Current, Single Pulse	I_{AS}	41.3	A
Avalanche Energy, Single Pulse ²⁾	E_{AS}	85.2	mJ
Power Dissipation	P_D	48	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	2.6	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	35	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.1 \text{ mH}$, $R_g = 25 \Omega$, $I_{AS} = 41.3 \text{ A}$, $V_{GS} = 10 \text{ V}$.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 1\text{ mA}$	BV_{DSS}	60	-	-	V
Drain-Source Leakage Current at $V_{DS} = 60\text{ V}$	I_{DSS}	-	-	1	μA
Gate-Source Leakage Current at $V_{GS} = \pm 20\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 120\text{ }\mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance at $V_{GS} = 10\text{ V}$, $I_D = 100\text{ A}$	$R_{DS(on)}$	-	2.8	3.2	$\text{m}\Omega$
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 5\text{ V}$, $I_D = 25\text{ A}$	g_{FS}	-	43.8	-	S
Gate resistance at $V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ V}$, $f = 1\text{ MHz}$	R_g	-	0.9	-	Ω
Input Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 30\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	5155	-	pF
Output Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 30\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	1756	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 30\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	39	-	pF
Total Gate Charge at $V_{DS} = 30\text{ V}$, $I_D = 25\text{ A}$, $V_{GS} = 10\text{ V}$	Q_g	-	82	-	nC
Gate Source Charge at $V_{DS} = 30\text{ V}$, $I_D = 25\text{ A}$, $V_{GS} = 10\text{ V}$	Q_{gs}	-	25	-	nC
Gate Drain Charge at $V_{DS} = 30\text{ V}$, $I_D = 25\text{ A}$, $V_{GS} = 10\text{ V}$	Q_{gd}	-	18	-	nC
Turn-On Delay Time at $V_{DS} = 30\text{ V}$, $I_D = 25\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 4.7\text{ }\Omega$	$t_{d(on)}$	-	46	-	ns
Turn-On Rise Time at $V_{DS} = 30\text{ V}$, $I_D = 25\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 4.7\text{ }\Omega$	t_r	-	69	-	ns
Turn-Off Delay Time at $V_{DS} = 30\text{ V}$, $I_D = 25\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 4.7\text{ }\Omega$	$t_{d(off)}$	-	32	-	ns
Turn-Off Fall Time at $V_{DS} = 30\text{ V}$, $I_D = 25\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 4.7\text{ }\Omega$	t_f	-	37	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_S = 100\text{ A}$, $V_{GS} = 0\text{ V}$	V_{SD}	-	-	1.3	V
Body-Diode Continuous Current	I_S	-	-	93	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	450	A
Body Diode Reverse Recovery Time at $I_S = 25\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	50	-	ns
Body Diode Reverse Recovery Charge at $I_S = 25\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	55	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

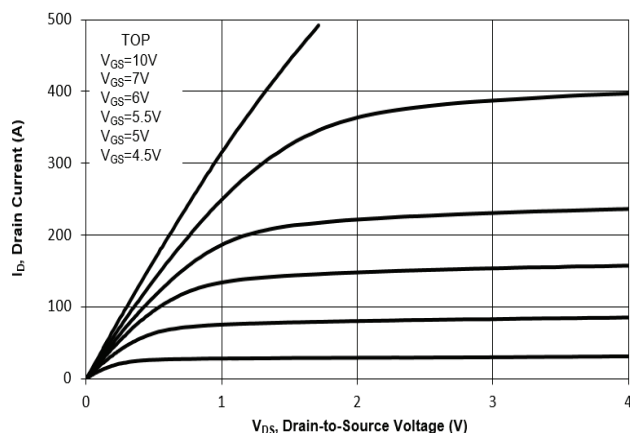


Fig. 2 Typical Transfer Characteristics

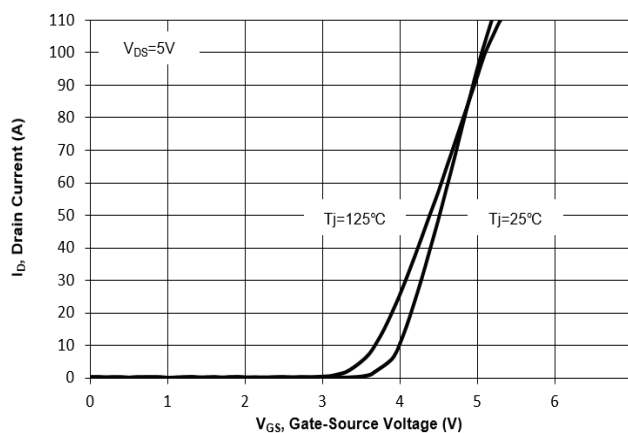


Fig. 3 On-Resistance vs. Drain Current

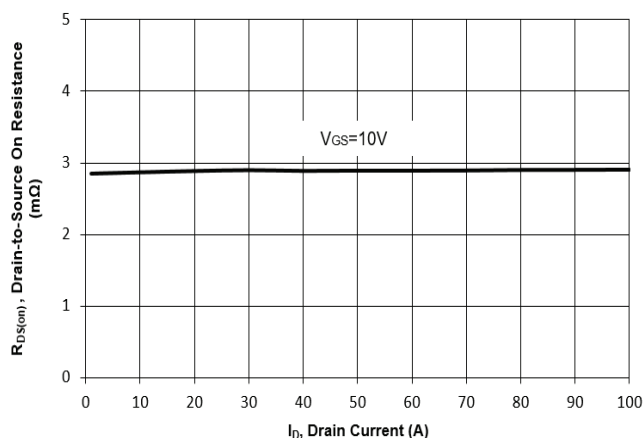


Fig. 4 On-Resistance vs. Gate to Source Voltage

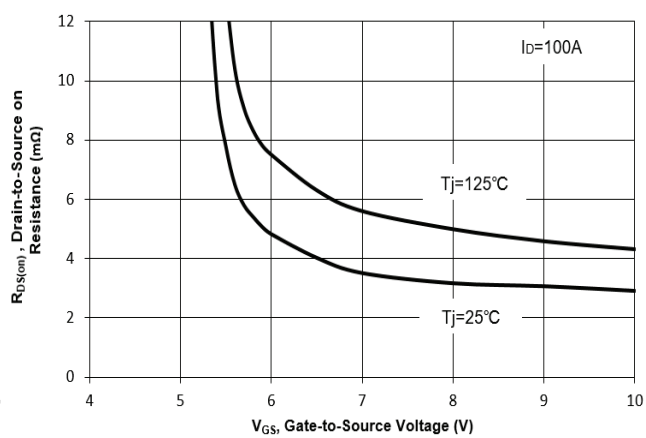


Fig. 5 On-Resistance vs. T_J

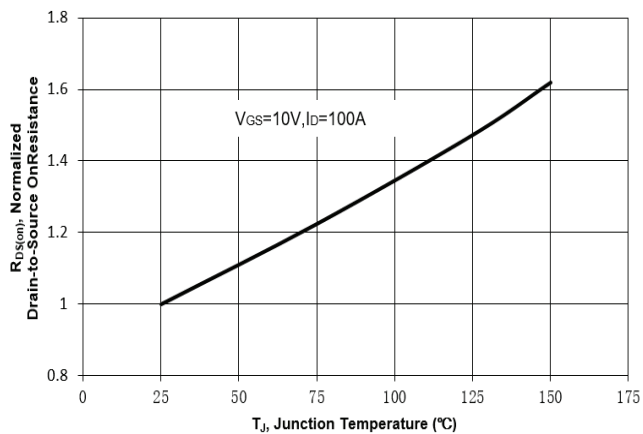
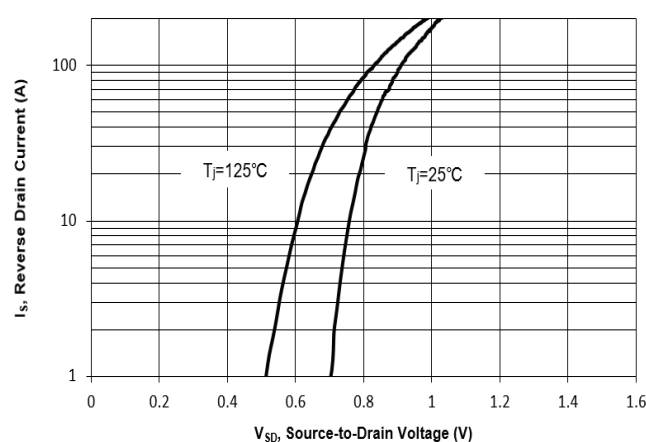


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

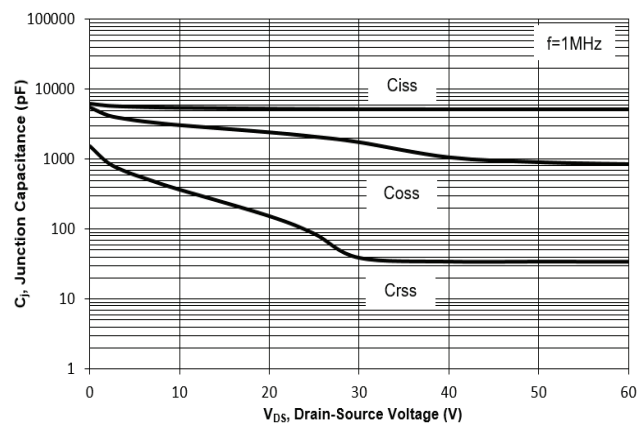


Fig. 8 Drain-Source Leakage Current vs. T_j

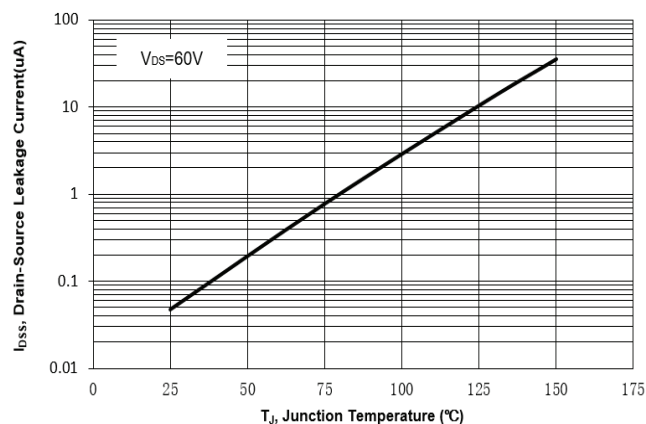


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

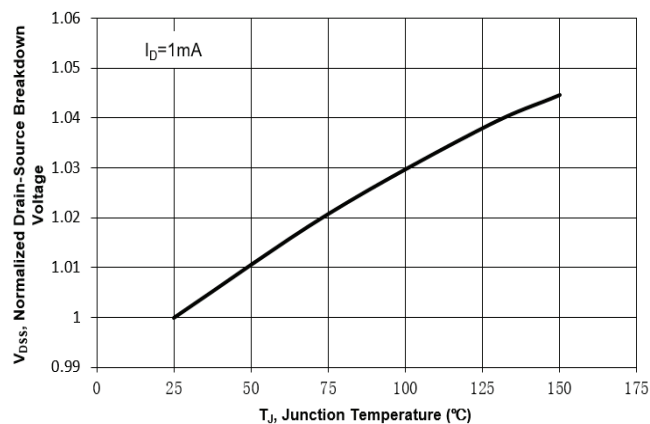


Fig. 10 Gate Threshold Variation vs. T_j

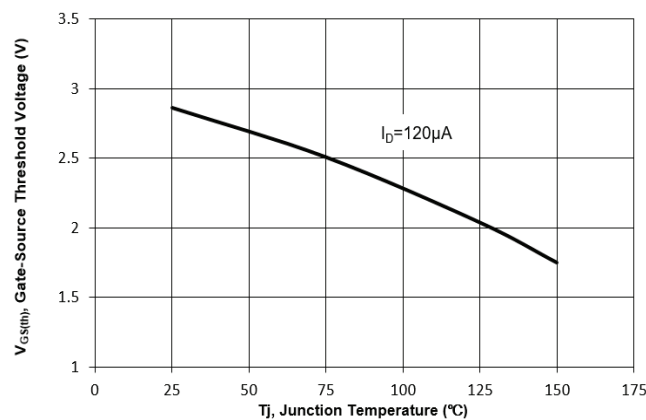


Fig. 11 Gate Charge

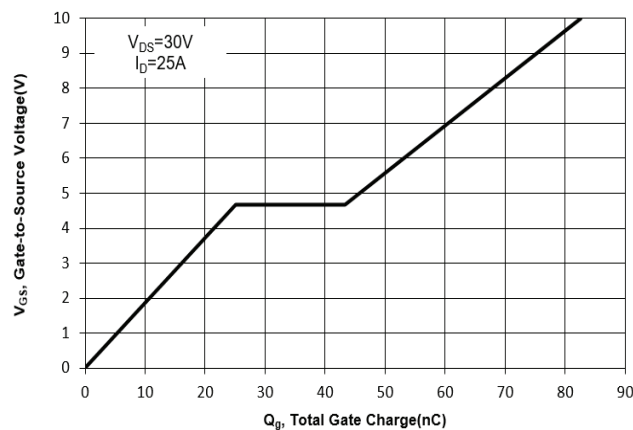
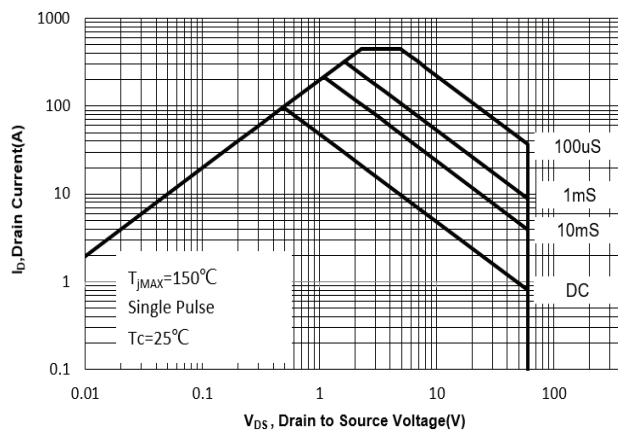


Fig. 12 Safe Operation Area



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)

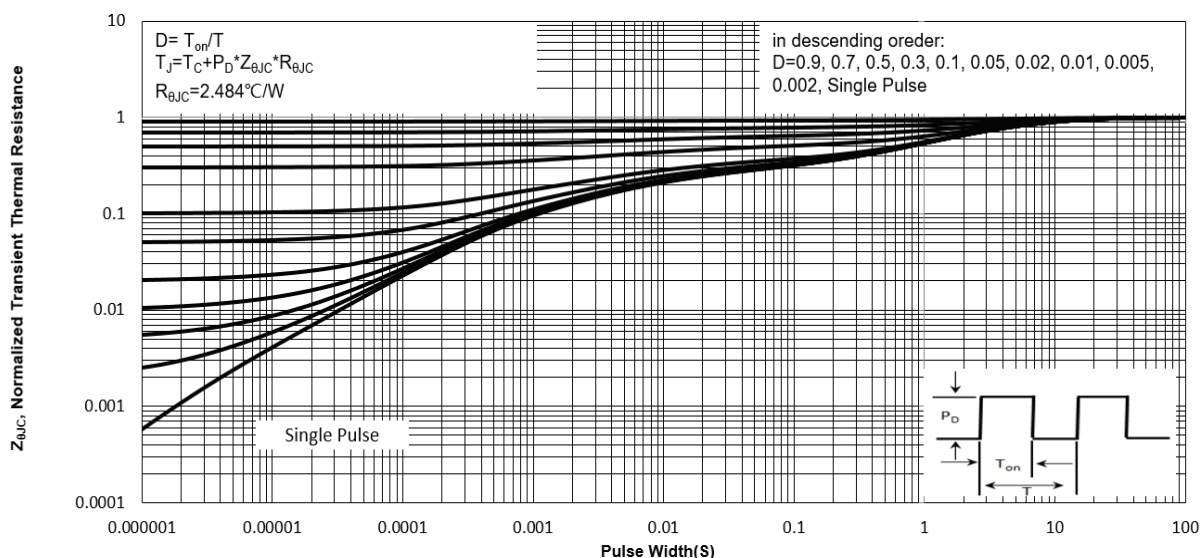
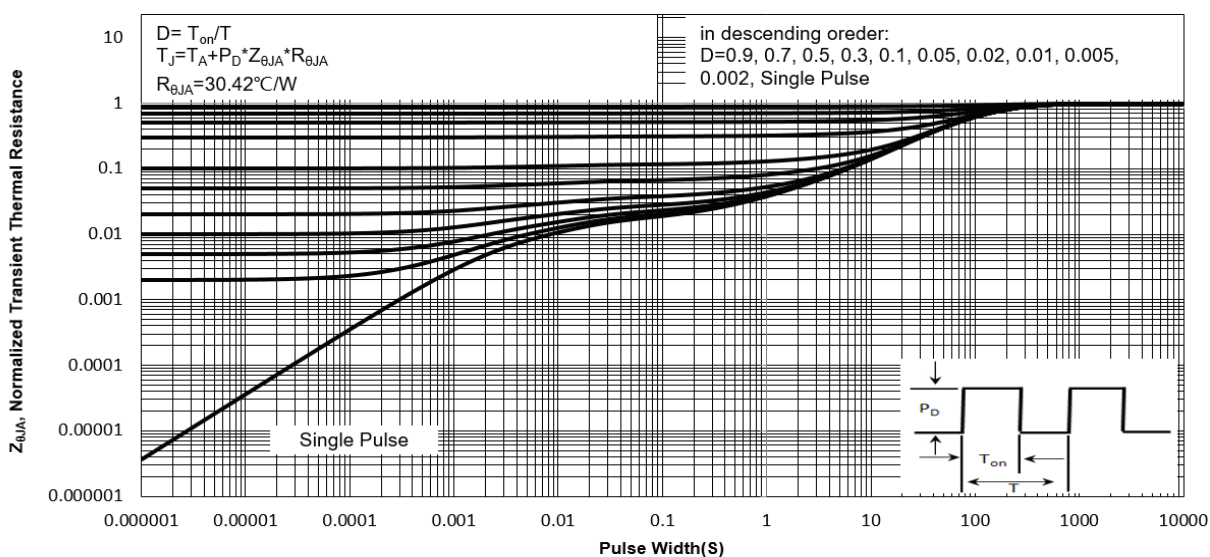
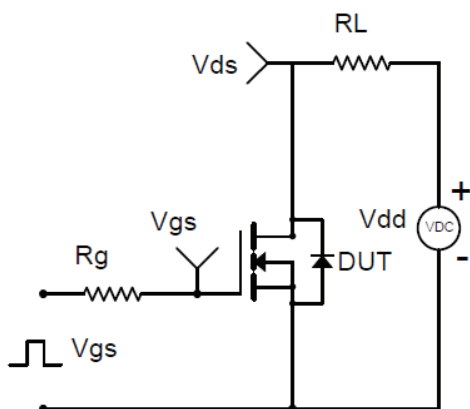
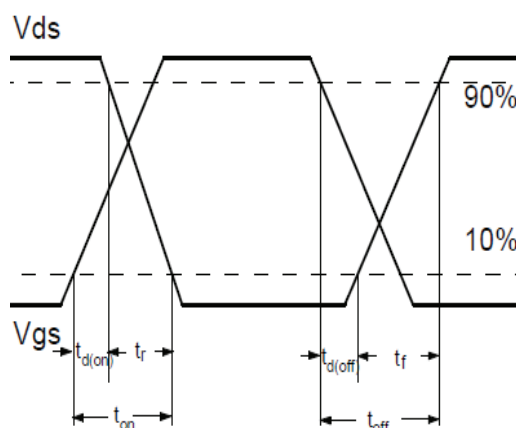
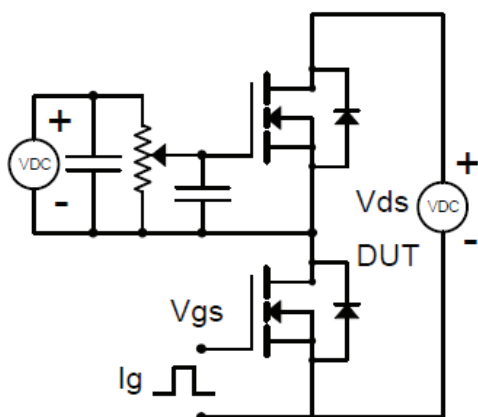
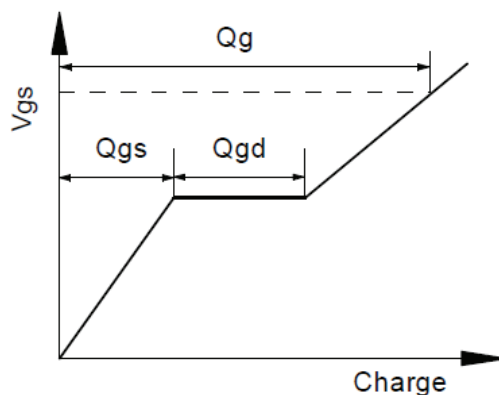
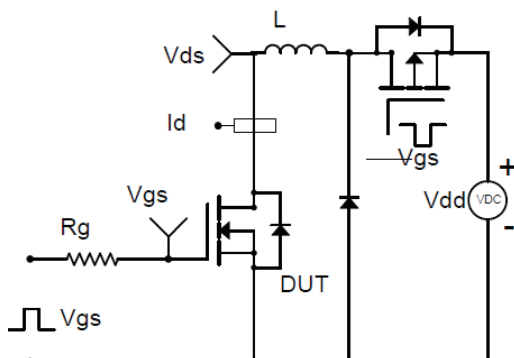
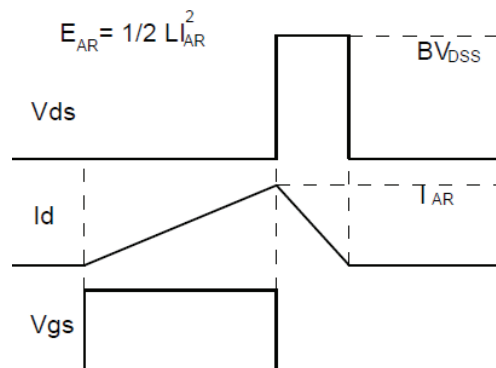


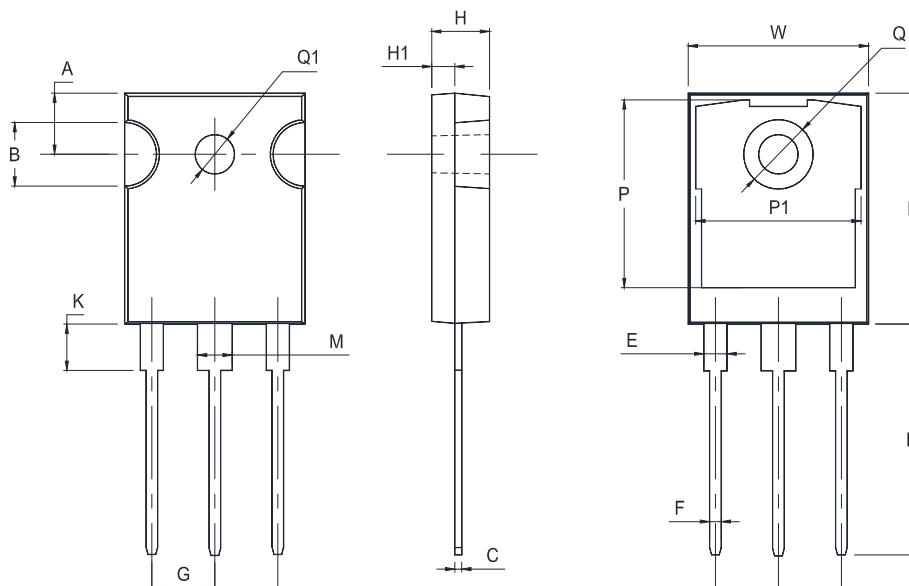
Fig. 14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)



Test Circuits
Fig.1-1 Switching times test circuit

Fig.1-2 Switching Waveform

Fig.2-1 Gate charge test circuit

Fig.2-2 Gate charge waveform

Fig.3-1 Avalanche test circuit

Fig.3-2 Avalanche waveform


Package Outline Dimensions (Units: mm)

TO-247



UNIT	A	B	C	D	E	F	G	W	H	H1	K	L	M	P
mm	6.5	5.2	0.7	20.3	2.2	1.3	5.7	16.2	5.3	2.5	4.45	21.3	3.2	16.6
	5.9	4.6	0.5	19.7	1.8	1.1	5.1	15.8	4.7	2.1	4.05	20.7	2.8	16.2

UNIT	P1	Q	Q1
mm	14.2	7.35	4.2
	13.8	7.05	3.6

Packing information

Package	Carton Quantity	Box Quantity	Base Quantity	Delivery Mode
TO-247	2.88 K / Carton	720 pcs / Box	30 pcs / Tube	Tube

Marking information

" TPT06N028S " = Part No
 " ***** " = Date Code Marking
 Font type: Arial



Disclaimer: Our company reserve the right to make modifications, enhancements, improvements, corrections or other changes to improve product design, functions and reliability, anytime without notice.